

v07.0418

GaAs InGaP HBT MMIC BROADBAND AMPLIFIER GAIN BLOCK, DC - 6 GHz

Typical Applications

Ideal as a Driver & Amplifier for:

- 2.2 2.7 GHz MMDS
- 3.5 GHz Wireless Local Loop
- 5 6 GHz UNII & HiperLAN

Features

P1dB Output Power: +14 dBm

Output IP3: +27 dBm

Gain: 17 dB

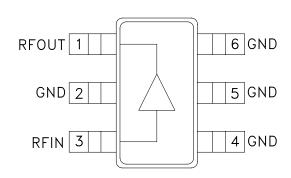
Single Supply: +5V

High Reliability GaAs HBT Process

Ultra Small Package: SOT26

Included in the HMC-DK001 Designer's Kit

Functional Diagram



General Description

The HMC313 & HMC313E are GaAs InGaP Heterojunction Bipolar Transistor (HBT) MMIC amplifiers that operate from a single Vcc supply. The surface mount SOT26 amplifier can be used as a broadband gain stage or used with external matching for optimized narrow band applications. With Vcc biased at +5V, the HMC313(E) offers 17 dB of gain and +15 dBm of saturated power while only requiring 50 mA of current.

Electrical Specifications, $T_A = +25$ °C, Vcc = +5.0V

Parameter -	Vcc = +5V			Linita
	Min.	Тур.	Max.	- Units
Frequency Range	DC - 6		GHz	
Gain	14	17	20	dB
Gain Variation Over Temperature		0.02	0.03	dB/°C
Input Return Loss		7		dB
Output Return Loss		6		dB
Reverse Isolation		30		dB
Output Power for 1 dB Compression (P1dB) @ 1.0 GHz	11	14		dBm
Saturated Output Power (Psat) @ 1.0 GHz		15		dBm
Output Third Order Intercept (IP3) @ 1.0 GHz	24	27		dBm
Noise Figure		6.5		dB
Supply Current (Icc)		50		mA

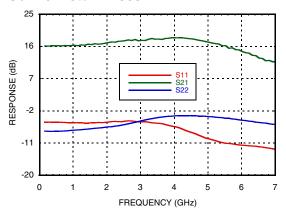
Note: Data taken with broadband bias tee on device output.



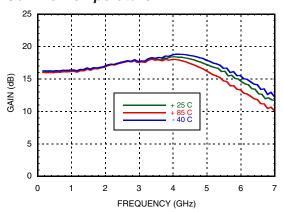
v07.0418

GaAs InGaP HBT MMIC BROADBAND AMPLIFIER GAIN BLOCK, DC - 6 GHz

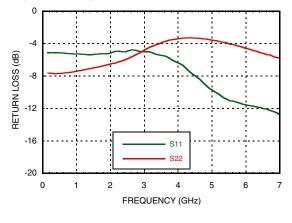
Gain & Return Loss



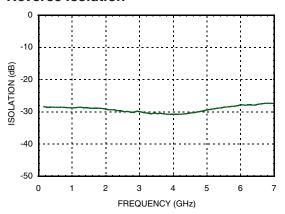
Gain vs. Temperature



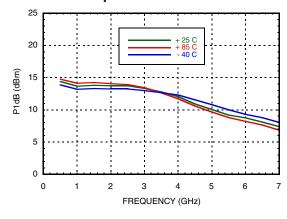
Input & Output Return Loss



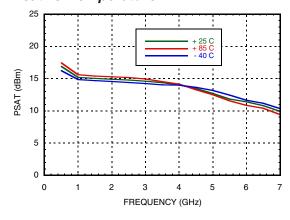
Reverse Isolation



P1dB vs. Temperature



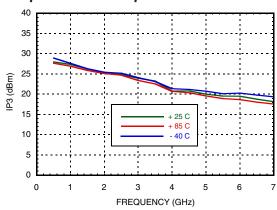
Psat vs. Temperature



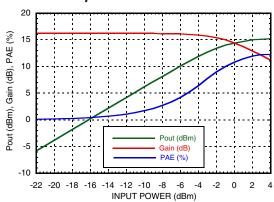


GaAs InGaP HBT MMIC BROADBAND AMPLIFIER GAIN BLOCK, DC - 6 GHz

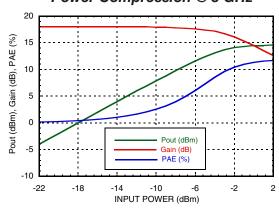
Output IP3 vs. Temperature



Power Compression @ 1 GHz



Power Compression @ 3 GHz





v07.0418

GaAs InGaP HBT MMIC BROADBAND AMPLIFIER GAIN BLOCK, DC - 6 GHz

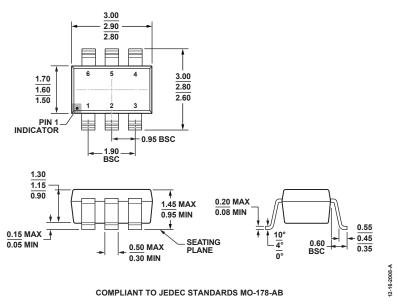
Absolute Maximum Ratings

Collector Bias Voltage (Vcc)	+5.5 Vdc	
RF Input Power (RFIN)(Vcc = +5Vdc)	+20 dBm	
Junction Temperature	150 °C	
Continuous Pdiss (T = 85 °C) (derate 3.99 mW/°C above 85 °C)	0.259 W	
Thermal Resistance (junction to pin 2 lead) [1]	251 °C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	
ESD Sensitivity (HBM)	Class 1A	



[1] Pin 2 REQUIRES good thermal attachment to the PCB

Outline Drawing



6-Lead Small Outline Transistor Package [SOT-23] (RJ-6)
Dimensions shown in millimeters.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]
HMC313	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H313 XXXX
HMC313TR	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	313 XXXX
HMC313E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	313E XXXX
HMC313ETR	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	313E XXXX

^[1] Max peak reflow temperature of 235 °C

^[2] Max peak reflow temperature of 260 °C

^{[3] 4-}Digit lot number XXXX



GaAs InGaP HBT MMIC BROADBAND AMPLIFIER GAIN BLOCK, DC - 6 GHz

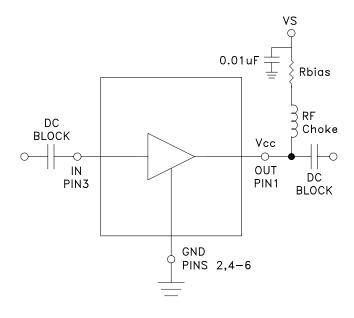
Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1	RFOUT	This pin is DC coupled. An off chip DC blocking capacitor is required.	RFOUT
3	RFIN	This pin is DC coupled. An off chip DC blocking capacitor is required.	
2, 4-6	GND	These pins must be connected to RF/DC ground.	GND =

Application Circuit

Recommended Bias Resistor Values for Icc = 50 mA, Rbias = (Vs - 5.0) / Icc

Supply Voltage (Vs)	5V	6V	8V
RBIAS VALUE	0 Ω	20 Ω	62 Ω
RBIAS POWER RATING		1/4 W	½ W



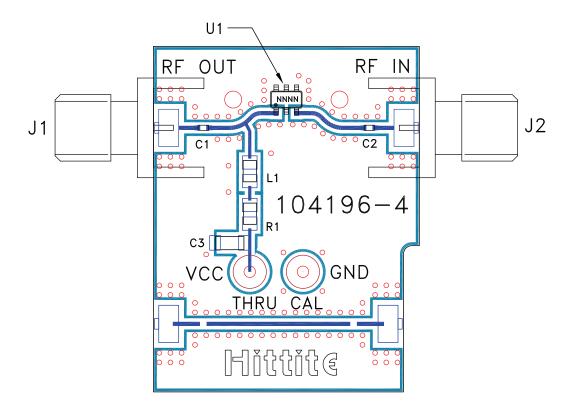
Note:

- 1. Select Rbias to achieve desired Vcc voltage on Pin 1.
- 2. External Blocking Capacitors are required on Pins 1 & 3.



GaAs InGaP HBT MMIC BROADBAND AMPLIFIER GAIN BLOCK, DC - 6 GHz

Evaluation PCB



List of Materials for Evaluation PCB 104217 [1]

Item	Description
J1 - J2	PCB Mount SMA Connector
C1 - C2	100 pF Capacitor, 0402 Pkg.
C3	100 pF Capacitor, 0805 Pkg.
L1	22 nH Inductor, 0805 Pkg.
R1	22 Ω Resistor, 0805 Pkg.
U1	HMC313 / HMC313E
PCB [2]	104196 Evaluation PCB

^[1] Reference this number when ordering complete evaluation PCB

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Analog Devices, upon request.

^[2] Circuit Board Material: Arlon 25FR or Roger 4350

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for RF Amplifier category:

Click to view products by Analog Devices manufacturer:

Other Similar products are found below:

A82-1 BGA622H6820XTSA1 BGA 728L7 E6327 BGB719N7ESDE6327XTMA1 HMC397-SX HMC405 HMC561-SX HMC8120-SX HMC8121-SX HMC-ALH382-SX HMC-ALH476-SX SE2433T-R SMA3101-TL-E SMA39 A66-1 A66-3 A67-1 A81-2 LX5535LQ LX5540LL MAAM02350 HMC3653LP3BETR HMC549MS8GETR HMC576-SX HMC-ALH435-SX SMA101 SMA32 SMA411 SMA531 SST12LP19E-QX6E WPM0510A HMC5879LS7TR HMC1087F10 HMC1086 HMC1016 SMA1212 MAX2689EWS+T MAAMSS0041TR MAAM37000-A1G LTC6430AIUF-15#PBF SMA70-2 SMA4011 A231 HMC-AUH232 LX5511LQ LX5511LQ-TR HMC7441-SX HMC-ALH310 XD1001-BD-000V A4011